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Author and Subject Index
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The Computer-Derived 1976 Journal Index

The Publication Committee of the Society recommended the use of a computer-derived index in 1968, and this practice is planned to be continued. This index is published two months earlier than the usual index and makes possible indexing more information than before. These indices refer only to *Journal* articles, reviews, brief communications, discussions, and news and reviews listed in the contents pages. They do not include meeting papers, abstracts, and news items. These indices were prepared for the *Journal* by the Institute for Scientific Information® , Philadelphia, Pennsylvania.

Using the Index

1. Given any author, go directly to his name in the author and title index to find the full paper title with a page citation or, if he is a secondary author, to find a cross-reference to a primary author.
2. Given any topic, go to the subject index and search for the key word itself.
3. For a detailed explanation of symbols and abbreviations, see the sample pages before the individual author and title index and the subject index.
4. Chemical formulae cannot be reproduced directly because the conventional computer printout appears in capital letters only. For example, B13 could be three atoms of bismuth or boron triiodide. To avoid this ambiguity, an attempt has been made to write out chemical formulae.
5. In the author index, an author is always listed with all available initials, which for lack of space sometimes can mean omission of one or two letters from the end of his last name. This truncation is indicated by a period at the end of the last name.

The Publication Committee will appreciate comments on the usefulness and accuracy of this index.

NEWTON SCHWARTZ
Chairman
Publication Committee

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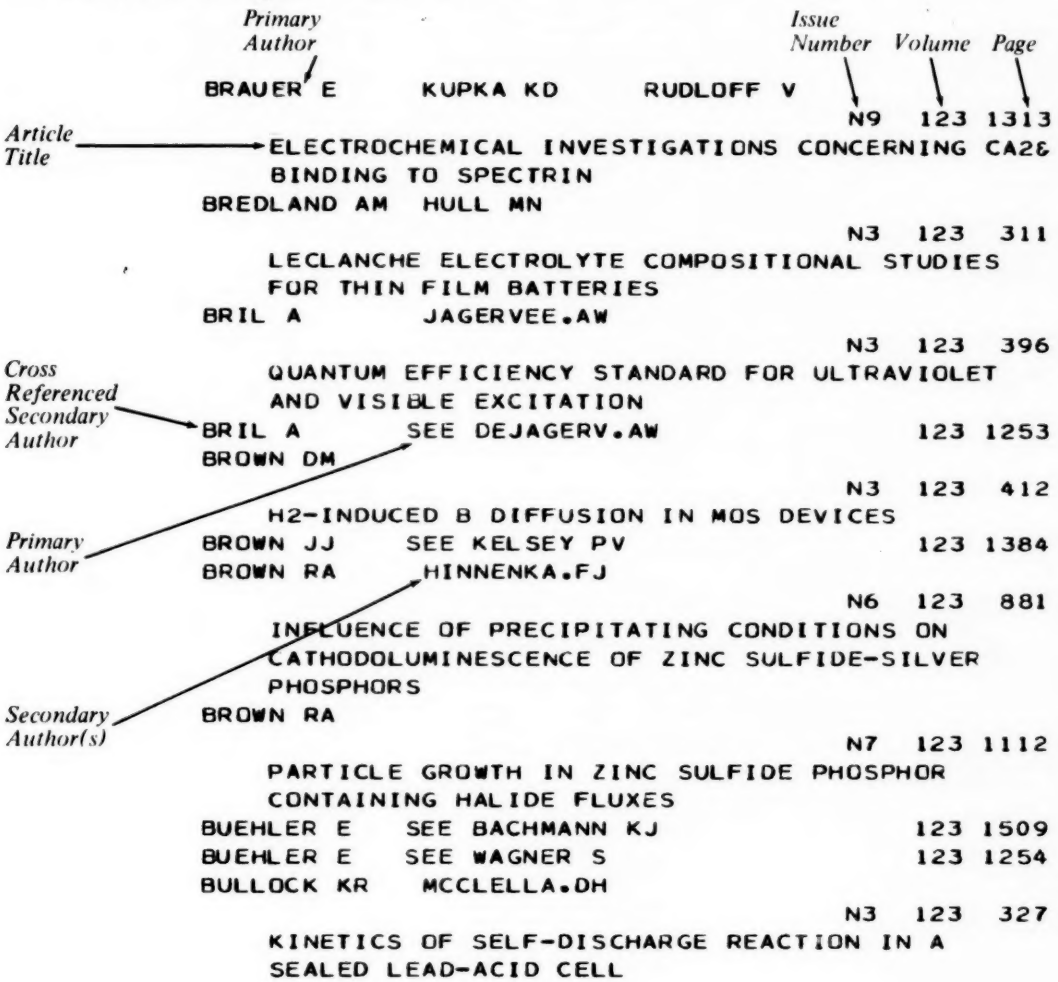
To locate a full description of a source item, look up the primary author. Under a given name, journal articles or primary authorship are described first. Items of secondary authorship follow. These are cross-referenced to the primary author whose name follows the word SEE.



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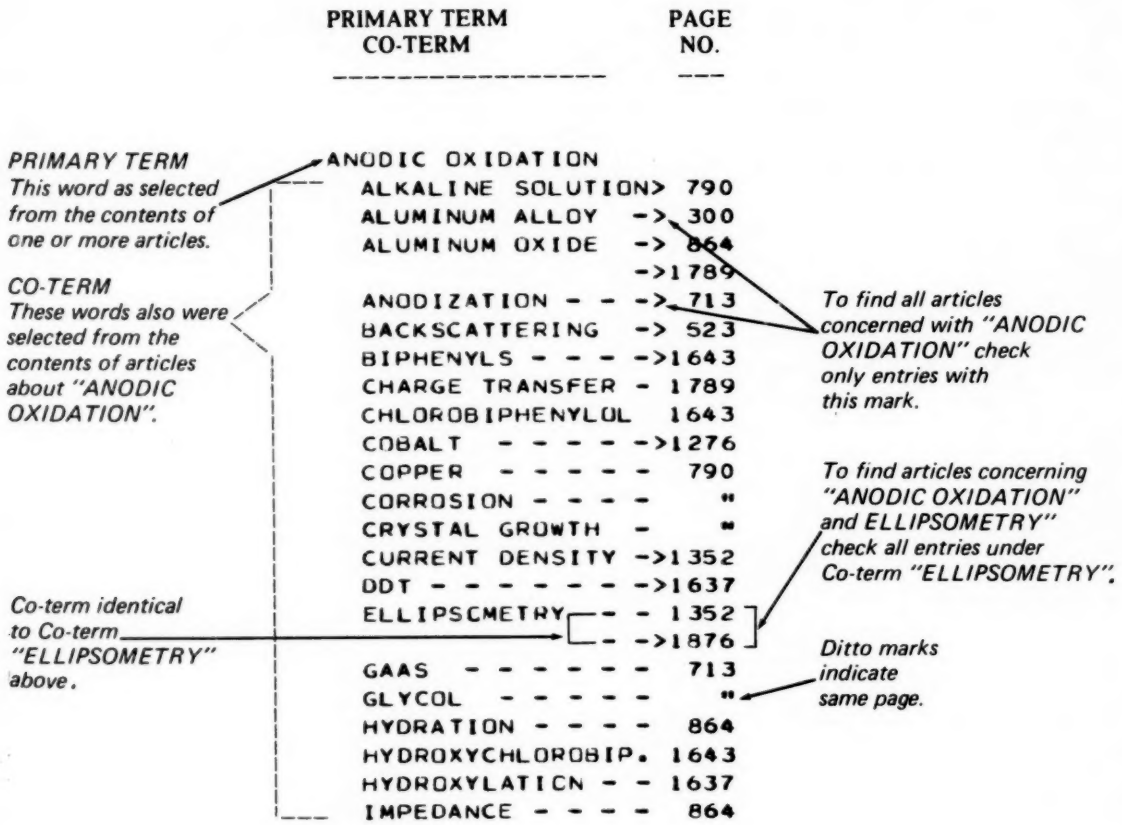
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